

## **TCS800**

### 800 Watts, 50 Volts, Pulsed Avionics 1030 MHz

### **GENERAL DESCRIPTION**

The TCS800 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1030 MHz, with the pulse width and duty required for TCAS applications. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

# CASE OUTLINE 55SM Style 1

### ABSOLUTE MAXIMUM RATINGS

**Maximum Power Dissipation** 

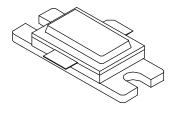
Device Dissipation @25°C<sup>1</sup> 1944 W

**Maximum Voltage and Current** 

 $\begin{array}{lll} \mbox{Collector to Base Voltage } (\mbox{BV}_{ces}) & 65 \ \mbox{V} \\ \mbox{Emitter to Base Voltage } (\mbox{BV}_{ebo}) & 3.5 \ \mbox{V} \\ \mbox{Collector Current } (\mbox{I}_c) & 50 \ \mbox{A} \\ \end{array}$ 

**Maximum Temperatures** 

Storage Temperature -65 to +200 °C Operating Junction Temperature +230 °C



### **ELECTRICAL CHARACTERISTICS @ 25°C**

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P <sub>out</sub>	Power Out	F = 1030 MHz	800			W
Pin	Power Input	$V_{CC} = 50 \text{ Volts}$			126	W
$P_{g}$	Power Gain	$PW = 32 \mu sec$	8.0	9.0		dB
$\eta_c$	Collector Efficiency	DF = 1%		45		%
$R_{L}$	Input Return Loss			-12		dB
Pd	Pulse Droop			0.5		dB
VSWR	Load Mismatch Tolerance	F = 1030  MHz			4:1	

#### **FUNCTIONAL CHARACTERISTICS @ 25°C**

BV <sub>ebo</sub> *	Emitter to Base Breakdown	Ie = 70  mA	3.5		V
$\mathrm{BV}_{\mathrm{ces}}$	Collector to Emitter Breakdown	Ic = 100  mA	65		V
h <sub>FE</sub> *	DC – Current Gain	Vce = 5V, $Ic = 5A$	20		
$\theta jc^1$	Thermal Resistance			0.09	°C/W

NOTE 1: At rated output power and pulse conditions.

\*: Not measurable due to internal EB returns

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Freq (MHz)	Zin	Zcl
1030	1.63+j1.59	0.47-j1.14

